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Linearity improvement for Broadband CMOS stacked Power Amplifiers With integrated Adaptive bias Circuit

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I. INTRODUCTION

In modern smart handheld devices, there is an explosive demand to handle an increased amount of information and content using the limited available frequency spectrum, such as LTE and worldwide inter-operability for microwave access (WIMAX). Since the modulated signals have high peak-to-average-power ratios (PAPR) with wide bandwidths, PAs should be operated at a back-off power from the peak to satisfy the linearity. Due to the serious level of efficiency degradation from the back-off operation, the linearization technique is crucial at a high power region.

II. DESIGN AND RESULTS

This paper applies an adaptive bias circuit to the bottom-TR of a stacked PA to improve linearity, using the 0.11- μm RF CMOS process. By using the bias circuit, as illustrated in Fig. 1, a sweet spot and peak average output power can be located as a deeper class-AB bias without any linearity distortion at the low-to-mid power region [1]. Considering bandwidth and output power, a stacked topology is employed in this paper and it is composed of four connected transistors in a series, as shown in Fig. 2 [2]. In Fig. 3, the PA with the integrated bias circuit improves 5 dB at the sweet spot of $\text{ACLR}_{\text{E-UTRA}}$, compared to the constant Class-AB bias PA and shows an average output power of 25.3 dBm, a PAE and DE of 21/29 %, with an $\text{ACLR}_{\text{E-UTRA}}$ of -30 dBc at 1.88 GHz for a LTE 10 MHz 16 QAM 7.5dB PAPR signal. Also, The PA delivers an average output power and

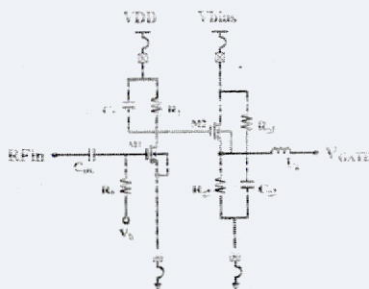


Fig. 1. Schematics of the adaptive bias circuit for the gate of the Bottom-TR.

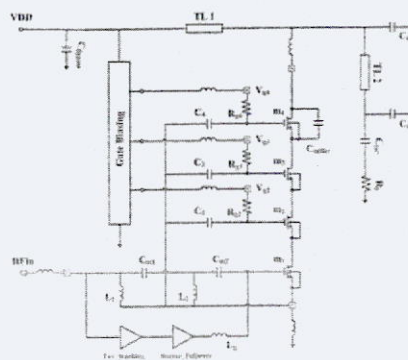


Fig. 2. Overall schematic of broadband 4-stacked PA with the adaptive bias circuit.

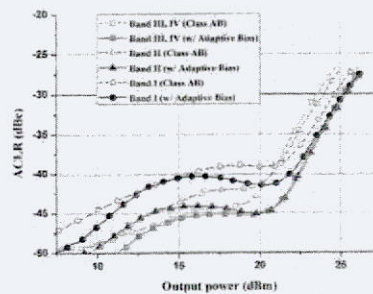


Fig. 3. Measured ACLRs of the designed PA using LTE signal at band I, II, III, and IV.

DE more than 24.5 dBm/25.6 % from 1.55 GHz to 2.05 GHz with the same bias condition. This adaptive bias circuit applied to a stacked PA is useful for broadband linear applications.

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